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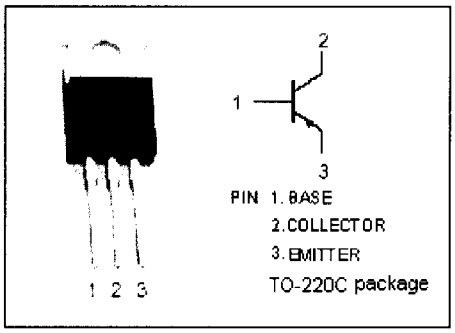
Silicon PNP Power Transistor — BD802

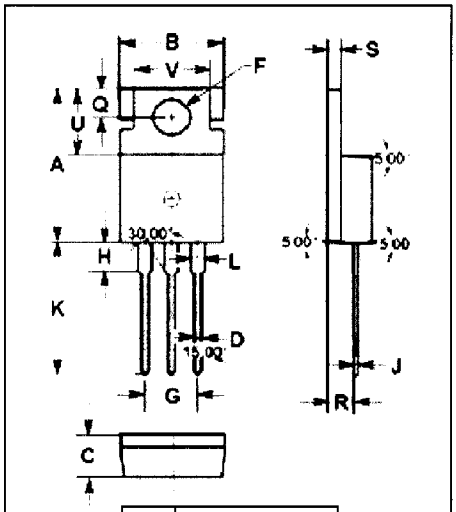
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = -100V(Min)
- Low Saturation Voltage
- Complement to Type BD801



APPLICATIONS

- Designed for a wide variety of medium-power switching and amplifier applications , such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_B	Base Current-Continuous	-3	A
P_C	Collector Power Dissipation T_C=25℃	65	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Ttemperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.92	℃/W

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -100mA; I_B= 0	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A ; V_{CE}= -2V			-1.6	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-1	mA
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -2V	30			
h_{FE-2}	DC Current Gain	I_C= -3A ; V_{CE}= -2V	15			
f_T	Current-Gain—Bandwidth Product	I_C= -0.25A ;V_{CE}= -10V,f_{test}= 1MHz	3			MHz